

# **BSS138AKA**

# **60 V, single N-channel Trench MOSFET**

29 April 2015

**Product data sheet** 

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage
- AEC-Q101 qualified

# 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

| Symbol                 | Parameter                        | Conditions  |     | Min | Тур | Max | Unit |
|------------------------|----------------------------------|---|-----|-----|-----|-----|------|
| $V_{DS}$               | drain-source voltage             | T <sub>j</sub> = 25 °C  |     | -   | -   | 60  | V    |
| $V_{GS}$               | gate-source voltage              |   |     | -20 | -   | 20  | V    |
| I <sub>D</sub>         | drain current                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C  | [1] | -   | -   | 200 | mA   |
| Static characteristics |                                  |   |     |     |     |     |      |
| R <sub>DSon</sub>      | drain-source on-state resistance | $V_{GS}$ = 10 V; $I_{D}$ = 100 mA; pulsed;<br>$t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C |     | -   | 2.7 | 4.5 | Ω    |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | G      | gate        | <u></u> 3          | D<br>I         |
| 2   | S      | source      |                    |                |
| 3   | D      | drain       | TO-236AB (SOT23)   | G S 017aaa255  |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package  |  |         |  |  |  |
|-------------|----------|--|---------|--|--|--|
|             | Name     | Description                              | Version |  |  |  |
| BSS138AKA   | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code [1] |
|-------------|------------------|
| BSS138AKA   | %JL              |

[1] % = placeholder for manufacturing site code

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter               | Conditions  |            | Min | Max  | Unit |  |
|--------------------|-------------------------|---|------------|-----|------|------|--|
| V <sub>DS</sub>    | drain-source voltage    | T <sub>j</sub> = 25 °C                            |            | -   | 60   | V    |  |
| $V_{GS}$           | gate-source voltage     |   |            | -20 | 20   | V    |  |
| I <sub>D</sub>     | drain current           | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C  | [1]        | -   | 200  | mA   |  |
|                    |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C | [1]        | -   | 125  | mA   |  |
| I <sub>DM</sub>    | peak drain current      | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs  |            | -   | 800  | mA   |  |
| P <sub>tot</sub>   | total power dissipation | T <sub>amb</sub> = 25 °C                          | <u>[2]</u> | -   | 300  | mW   |  |
|                    |                         |   | [1]        | -   | 360  | mW   |  |
|                    |                         | T <sub>sp</sub> = 25 °C                           |            | -   | 1060 | mW   |  |
| Tj                 | junction temperature    |   |            | -55 | 150  | °C   |  |
| T <sub>amb</sub>   | ambient temperature     |   |            | -55 | 150  | °C   |  |
| T <sub>stg</sub>   | storage temperature     |   |            | -65 | 150  | °C   |  |
| Source-drain diode |                         |   |            |     |      |      |  |
| Is                 | source current          | T <sub>amb</sub> = 25 °C                          | [1]        | -   | 200  | mA   |  |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

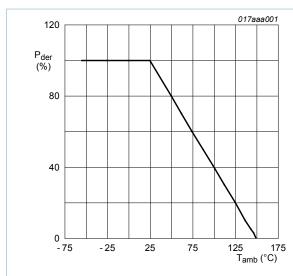


Fig. 1. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25\%)}} \times \ \mathbf{100} \ \%$$

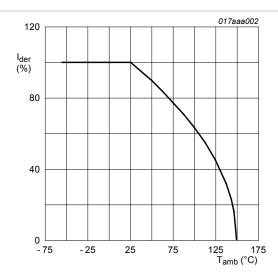


Fig. 2. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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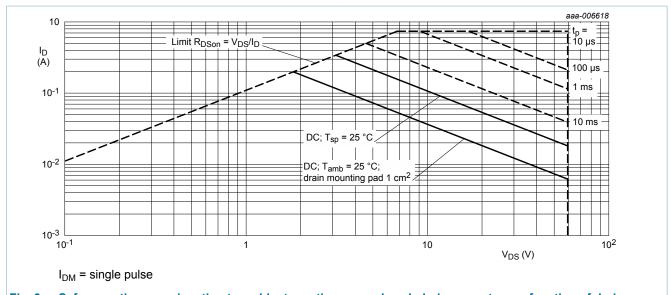


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol                | Parameter  | Conditions |     | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|-----|------|
| uig-a)                | thermal resistance<br>from junction to<br>ambient      |            | [1] | -   | 350 | 400 | K/W  |
|                       |  |            | [2] | -   | 300 | 340 | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance<br>from junction to solder<br>point |            |     | -   | -   | 115 | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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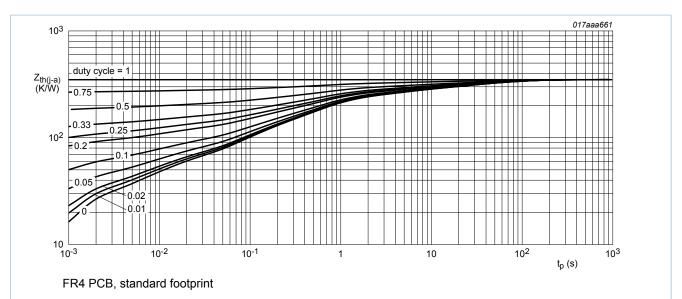


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

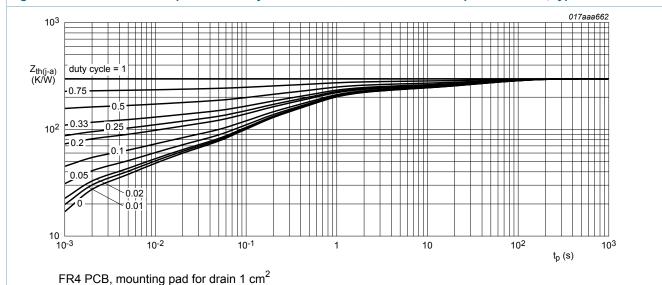


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 10. Characteristics

Table 7. Characteristics

| Table 7. C<br>Symbol | Parameter                        | Conditions   | Min    | Тур  | Max   | Unit |
|----------------------|----------------------------------|--|--------|------|-------|------|
| Static chara         |                                  | Conditions   | IVIIII | Тур  | IVIAA | Onit |
| V <sub>(BR)DSS</sub> | drain-source                     | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C                                     | 60     |      |       | V    |
| <b>v</b> (BK)D22     | breakdown voltage                | 1D = 250 μ/λ, VGS = 0 V, 1] = 25 0   | 00     |      |       | V    |
| $V_{GSth}$           | gate-source threshold voltage    | $I_D = 250 \text{ A}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$  | 0.8    | 1.2  | 1.5   | V    |
| I <sub>DSS</sub>     | drain leakage current            | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                      | -      | -    | 1     | μA   |
|                      |                                  | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C                                     | -      | -    | 10    | μA   |
| I <sub>GSS</sub>     | gate leakage current             | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                      | -      | -    | 3.5   | μA   |
|                      |                                  | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                     | -      | -    | -3.5  | μA   |
|                      |                                  | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                      | -      | -    | 1     | μΑ   |
|                      |                                  | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                     | -      | -    | -1    | μA   |
|                      |                                  | V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                                     | -      | -    | 0.5   | μA   |
|                      |                                  | $V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C   | -      | -    | -0.5  | μA   |
| R <sub>DSon</sub>    | drain-source on-state resistance | $V_{GS}$ = 10 V; $I_{D}$ = 100 mA; pulsed;<br>$t_{p} \le$ 300 µs; $\bar{\delta} \le$ 0.02; $T_{j}$ = 25 °C | -      | 2.7  | 4.5   | Ω    |
|                      |                                  | $V_{GS}$ = 10 V; $I_{D}$ = 100 mA; pulsed;<br>$t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{j}$ = 150 °C      | -      | 5.5  | 9.2   | Ω    |
|                      |                                  | $V_{GS}$ = 4.5 V; $I_{D}$ = 100 mA; pulsed;<br>$t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C | -      | 3    | 5.2   | Ω    |
|                      |                                  | $V_{GS}$ = 2.5 V; $I_{D}$ = 10 mA; pulsed;<br>$t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C  | -      | 4    | 13    | Ω    |
| 9fs                  | forward<br>transconductance      | $V_{DS}$ = 10 V; $I_{D}$ = 150 mA; pulsed;<br>$t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C  | 320    | -    | -     | mS   |
| Dynamic ch           | naracteristics                   |  |        |      |       |      |
| Q <sub>G(tot)</sub>  | total gate charge                | V <sub>DS</sub> = 30 V; I <sub>D</sub> = 150 mA; V <sub>GS</sub> = 4.5 V;                                  | -      | 0.39 | 0.51  | nC   |
| $Q_{GS}$             | gate-source charge               | T <sub>j</sub> = 25 °C   | -      | 0.1  | -     | nC   |
| $Q_{GD}$             | gate-drain charge                |  | -      | 0.1  | -     | nC   |
| C <sub>iss</sub>     | input capacitance                | V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;  | -      | 13   | 20    | pF   |
| C <sub>oss</sub>     | output capacitance               | T <sub>j</sub> = 25 °C   | -      | 2.6  | -     | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance     |  | -      | 1.1  | -     | pF   |
| d(on)                | turn-on delay time               | $V_{DS}$ = 40 V; $R_{L}$ = 250 $\Omega$ ; $V_{GS}$ = 10 V;   | -      | 5    | 10    | ns   |
| t <sub>r</sub>       | rise time                        | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$   | -      | 6    | -     | ns   |
| d(off)               | turn-off delay time              |  | -      | 36   | 72    | ns   |

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| Symbol             | Parameter            | Conditions                                    |  | Min  | Тур | Max | Unit |
|--------------------|----------------------|---|--|------|-----|-----|------|
| t <sub>f</sub>     | fall time            |   |  | -    | 22  | -   | ns   |
| Source-drain diode |                      |   |  |      |     |     |      |
| V <sub>SD</sub>    | source-drain voltage | $I_S$ = 115 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C |  | 0.47 | 0.7 | 1.2 | V    |

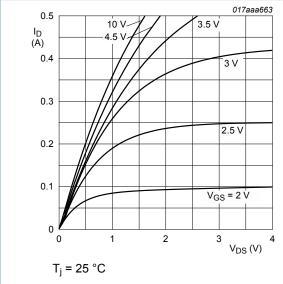


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

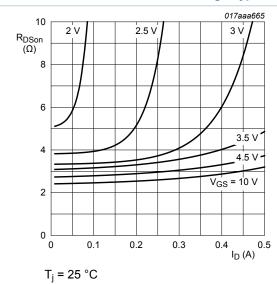


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

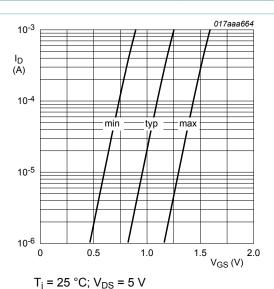


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

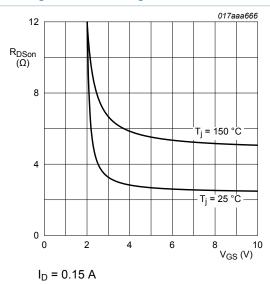


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 60 V, single N-channel Trench MOSFET

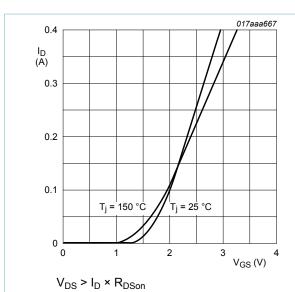


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

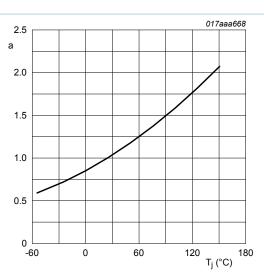


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

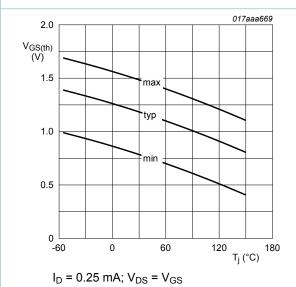
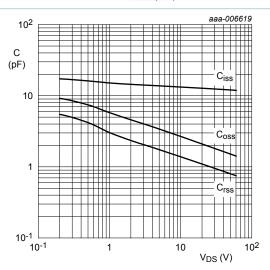


Fig. 12. Gate-source threshold voltage as a function of junction temperature

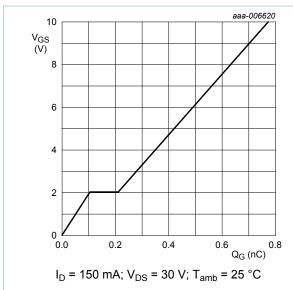


 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V<sub>DS</sub> - $V_{GS(pl)}$ V<sub>GS(th)</sub>  $V_{\mathsf{GS}}$  . Q<sub>GS1</sub> Q<sub>GS2</sub> -Q<sub>GS</sub> -Q<sub>GD</sub>-Q<sub>G(tot)</sub> 017aaa137

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

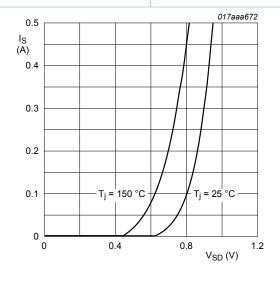
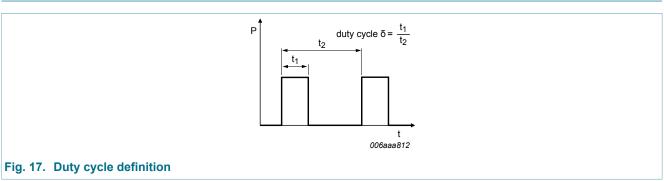


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

 $V_{GS} = 0 V$ 



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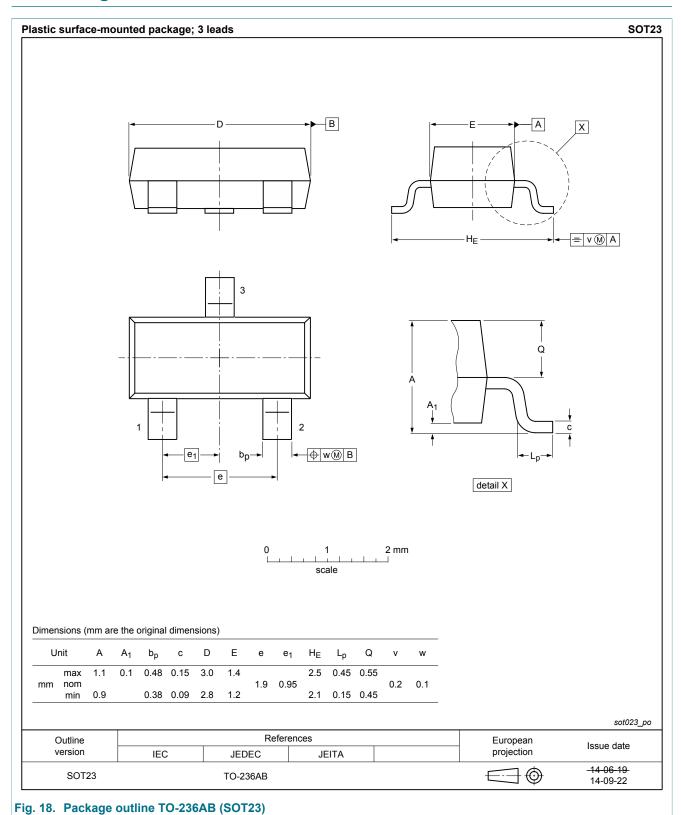
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### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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# 12. Package outline

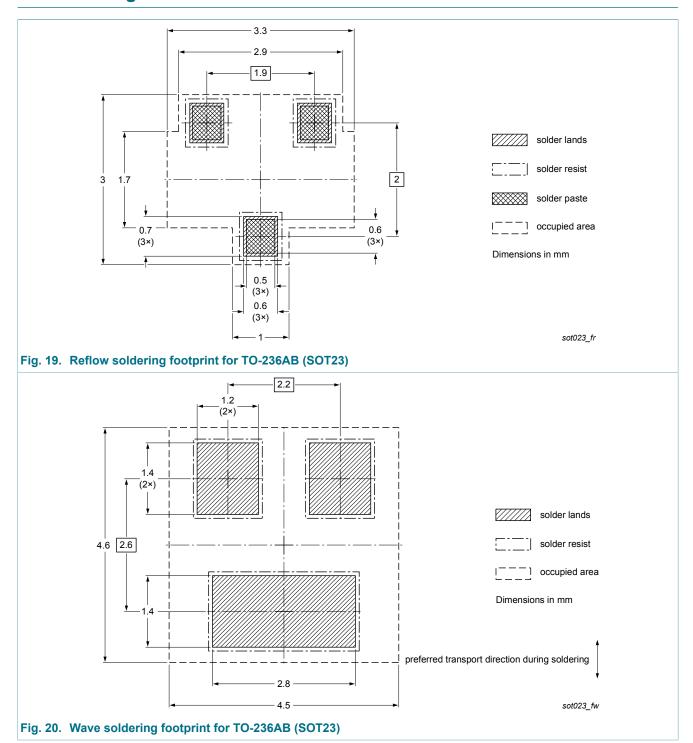


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### 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

| Data sheet ID  | Release date         | Data sheet status                 | Change notice | Supersedes    |  |  |  |
|----------------|----------------------|-----------------------------------|---------------|---------------|--|--|--|
| BSS138AKA v.3  | 20150429             | Product data sheet                | -             | BSS138AKA v.2 |  |  |  |
| Modifications: | Figure 14: x-axis so | Figure 14: x-axis scale corrected |               |               |  |  |  |
| BSS138AKA v.2  | 20141103             | Product data sheet                | -             | BSS138AKA v.1 |  |  |  |
| BSS138AKA v.1  | 20130206             | Product data sheet                | -             | -             |  |  |  |

#### 60 V, single N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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